

**SOT-23 Formed SMD Package**

**CMBT4401**

**SILICON PLANAR EPITAXIAL TRANSISTOR**

*N-P-N transistor*

**Marking**

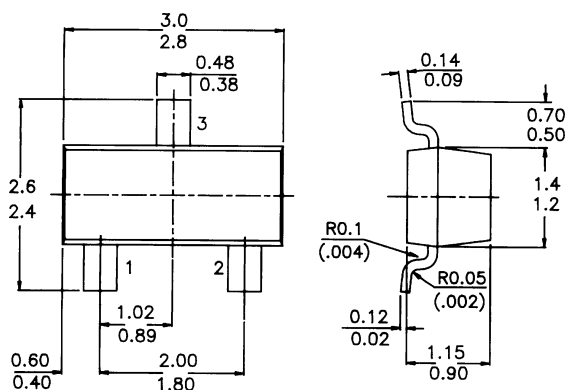
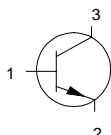
CMBT4401 = 2X

**PACKAGE OUTLINE DETAILS**

ALL DIMENSIONS IN mm

**Pin configuration**

1 = BASE  
2 = EMITTER  
3 = COLLECTOR



**ABSOLUTE MAXIMUM RATINGS**

Collector-emitter voltage	$V_{CEO}$	max.	40 V
Collector current (DC)	$I_C$	max.	600 mA
DC current gain	$h_{FE}$	min.	100
		max.	300
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	max	250 mW

**RATINGS** (at  $T_A = 25^\circ\text{C}$  unless otherwise specified)

**Limiting values**

Collector-emitter voltage	$V_{CEO}$	max.	40 V
Collector-base voltage	$V_{CBO}$	max.	60 V
Emitter-base voltage	$V_{EBO}$	max.	6 V
Collector current (DC)	$I_C$	max.	600 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	max	250 mW
Storage temperature range	$T_{stg}$		-55 to +150 $^\circ\text{C}$
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$

**CMBT4401****THERMAL RESISTANCE**

From junction to ambient

$$R_{th\ j-a} = 500\ \text{K/W}$$

**CHARACTERISTICS** $T_{amb} = 25\ ^\circ\text{C}$  unless otherwise specified

Collector-emitter breakdown voltage

$$I_C = 1.0\ \text{mA}; I_B = 0$$

$$V_{(BR)CEO} > 40\ \text{V}$$

Collector-base breakdown voltage

$$I_C = 100\ \mu\text{A}; I_E = 0$$

$$V_{(BR)CBO} > 60\ \text{V}$$

Emitter-base breakdown voltage

$$I_E = 100\ \mu\text{A}; I_C = 0$$

$$V_{(BR)EBO} > 6\ \text{V}$$

Base cut-off current

$$V_{CE} = 35\ \text{V}; V_{EB} = 0.4\ \text{V}$$

$$I_{BEX} < 0.1\ \mu\text{A}$$

Collector cut-off current

$$V_{CE} = 35\ \text{V}; V_{EB} = 0.4\ \text{V}$$

$$I_{CEX} < 0.1\ \mu\text{A}$$

D.C. current gain

$$I_C = 0.1\ \text{mA}; V_{CE} = 1\ \text{V}$$

$$h_{FE} > 20$$

$$I_C = 1.0\ \text{mA}; V_{CE} = 1\ \text{V}$$

$$h_{FE} > 40$$

$$I_C = 10\ \text{mA}; V_{CE} = 1\ \text{V}$$

$$h_{FE} > 80$$

$$I_C = 150\ \text{mA}; V_{CE} = 1\ \text{V}$$

$$h_{FE} \quad 100\ \text{to}\ 300$$

$$I_C = 500\ \text{mA}; V_{CE} = 2\ \text{V}$$

$$h_{FE} > 40$$

Saturation voltage

$$I_C = 150\ \text{mA}; I_B = 15\ \text{mA}$$

$$V_{CEsat} < 0.4\ \text{V}$$

$$V_{BEsat} \quad 0.75\ \text{to}\ 0.95\ \text{V}$$

$$I_C = 500\ \text{mA}; I_B = 50\ \text{mA}$$

$$V_{CEsat} < 0.75\ \text{V}$$

$$V_{BEsat} < 1.2\ \text{V}$$

Transition frequency

$$f = 100\ \text{MHz}; I_C = 20\ \text{mA}; V_{CE} = 10\ \text{V}$$

$$f_T > 250\ \text{MHz}$$

Collector-base capacitance

$$I_E = 0; V_{CB} = 5\ \text{V}; f = 100\ \text{kHz}$$

$$C_{cb} < 8\ \text{pF}$$

Emitter-base capacitance

$$I_C = 0; V_{BE} = 0.5\ \text{V}; f = 100\ \text{kHz}$$

$$C_{eb} < 30\ \text{pF}$$

Input impedance;  $f = 1\ \text{kHz}$ ;

$$I_C = 1\ \text{mA}; V_{CE} = 10\ \text{V}$$

$$h_{ie} \quad \begin{matrix} \text{min.} & 1\ \text{k}\Omega \\ \text{max.} & 8\ \text{k}\Omega \end{matrix}$$

Voltage feed-back ratio

$$I_C = 1\ \text{mA}; V_{CE} = 10\ \text{V}; f = 1\ \text{kHz}$$

$$h_{re} \quad \begin{matrix} \text{min.} & 0.1 \times 10^{-4} \\ \text{max.} & 30 \times 10^{-4} \end{matrix}$$

Small-signal current gain;  $f = 1\ \text{kHz}$ ;

$$I_C = 1\ \text{mA}; V_{CE} = 10\ \text{V}$$

$$h_{fe} \quad \begin{matrix} \text{min.} & 40 \\ \text{max.} & 500 \end{matrix}$$

**CMBT4401***Output admittance;  $f = 1 \text{ kHz}$ ;* $I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}$ 

$h_{oe}$	<i>min.</i>	$1 \text{ } \mu\text{S}$
	<i>max.</i>	$30 \text{ } \mu\text{S}$

*Switching times (resistive load)**Turn-on time* $I_C = 150 \text{ mA}; I_{B1} = 15 \text{ mA};$  $V_{CC} = 30 \text{ V}; V_{EB} = 2 \text{ V}$ *delay time*

$t_d$	<i>max.</i>	$15 \text{ ns}$
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*rise time*

$t_r$	<i>max.</i>	$20 \text{ ns}$
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*Turn-off time* $I_C = 150 \text{ mA}; V_{CC} = 30 \text{ V};$  $I_{B1} = I_{B2} = 15 \text{ mA}$ *storage time*

$t_s$	<i>max.</i>	$225 \text{ ns}$
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*fall time*

$t_f$	<i>max.</i>	$30 \text{ ns}$
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**Disclaimer**

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